

**Notice of References Cited**

Application/Control No.

09/749,590

Applicant(s)/Patent Under  
Reexamination  
OHTAKE ET AL

Examiner

Anh D. Mai

Art Unit

2814

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	C	US-			
	D	US-			
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	L	US-			
	M	US-			

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